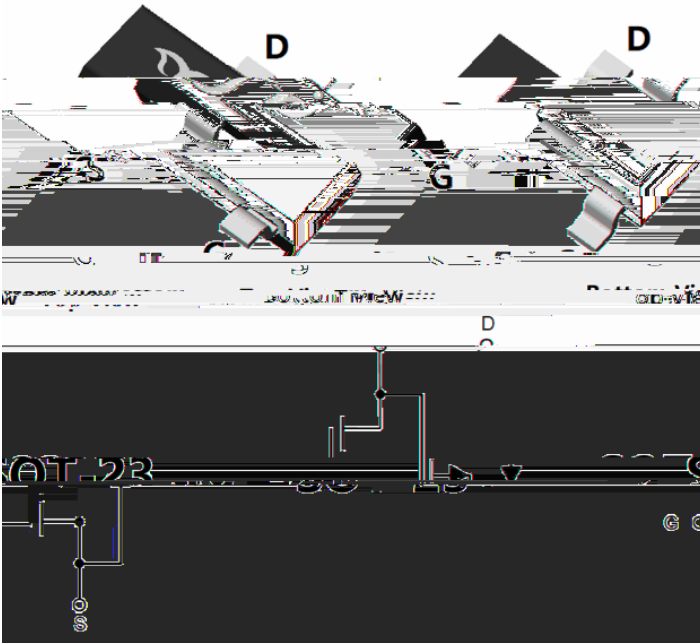




YJL2305BQ

RoHS
COMPLIANT

P-Channel Enhancement Mode Field Effect Transistor



Product Summary

" 96
" ,
" 56 21 DW 9 9 Ø PRKP
" 56 21 DW 9 9 Ø PRKP
" 56 21 DW 9 9 Ø PRKP

General Description

" 7UHQFK 3RZHU /9 026)(7 WHFKQRORJ\
" +LJK 3RZHU DQG &XUUHQW KDQGLQJ F
" /RZ *DWH &KDUJH
" 3DUW QR ZLWKHDXQVL\$(%4 TXDOLILH

Applications

" %DWWHU\ SURWHFWLRQ
" 3RZHU PDQDJHPHQW
" /RDG VZLWFK

vAbsolute Maximum Ratings 7s À |nÆÇvG...ÛE (•€E4 0" ò"4 b 9!v9 ûy€~2S,,c, • 0 \$

	7s -			
3XOVHG 'UDLQ &XUUHQW		'0		
7RWDO 3RZHU 'LVVLSDWLRQ	7s - 7s -	3		:
7KHUPDO 5HVLVWDQFH -XQFWLRQ WR \$PELHQW	-s			- :
-XQFWLRQ DQG 6WRUDJH 7HPSHUDWXUH 5DQJH - 77*			7	-

vOrdering Information ([DP SOH

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
< - / % 4	)	%6				3 UHHO



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vElectrical Characteristics 7 XQOHVV RWKHUZZLVH QRWHG

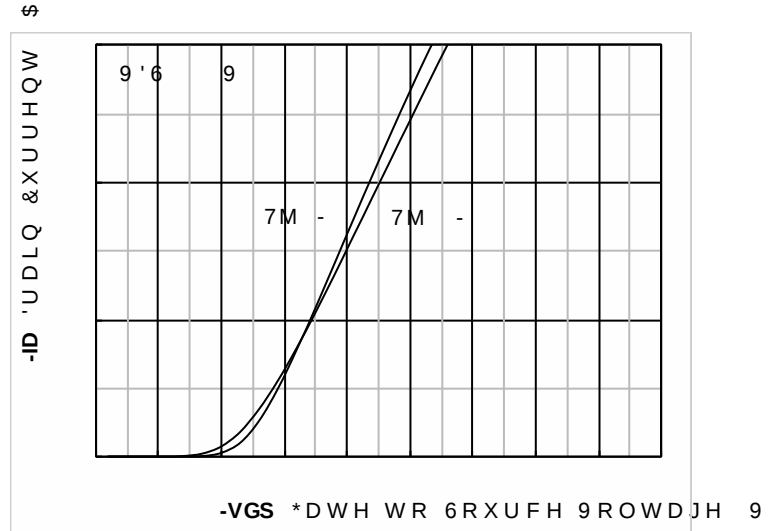
Parameter	Symbol	Conditions	Min	Typ	Max	
Static Parameter						
'UDLQ 6RXUFH %UHDNGRZQ 9ROWDJH		* ₆ 9%9 \$	9			9
-HHP *DWH 9ROWDJH 'UDLQ &XUHHQW		9 ₆ 9 9 9 7M				
		9 ₆ 9 9 9 7M				
*DWH %RG\ /HDNDJH &XUHHQW * ₆₆		" 9 .9 9	9		"	
*DWH 7KUHVKROG 9ROWDJH	* ₆ WK	9 ₆ ', \$	9			9

6WDWLF 'UDLQ 6RXUFH 2Q 5HVLVWDQFH

5

YJL2305BQ

■ Typical Performance Characteristics



) L J X U H 2 X W S X W W & K D U D F W

)LJXUH 7UDQVIHU &K

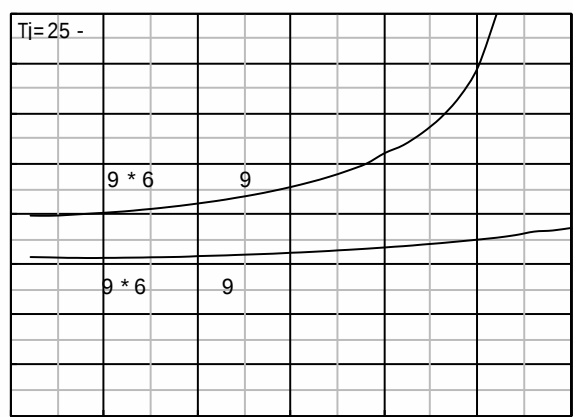
[illegible]

)LJXUH &DSDFLWDQFH &KDUDFWHULVWLQV)LJXUH *DWH &KD

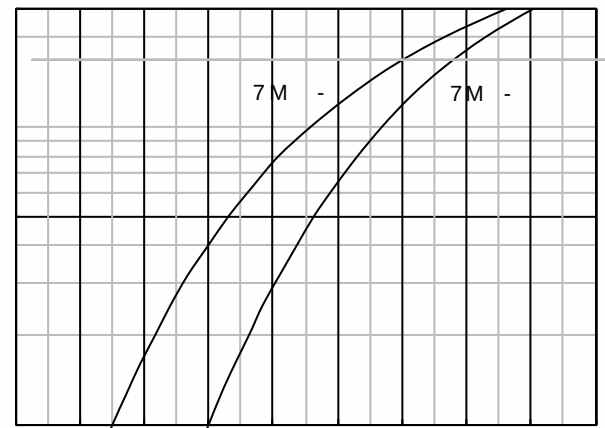
)LJXUH 2Q 5HVLVWDQFH 6RXUDH 9ROWDJH)LJXUHLJH 2QD5HVLVWDQFH



YJL2305BQ



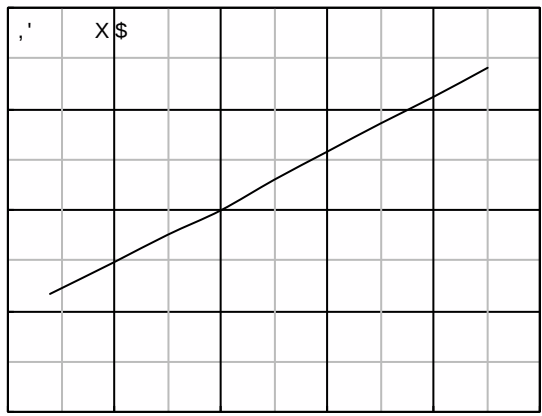
I_D - 'UDLQ & XUHHQW \$



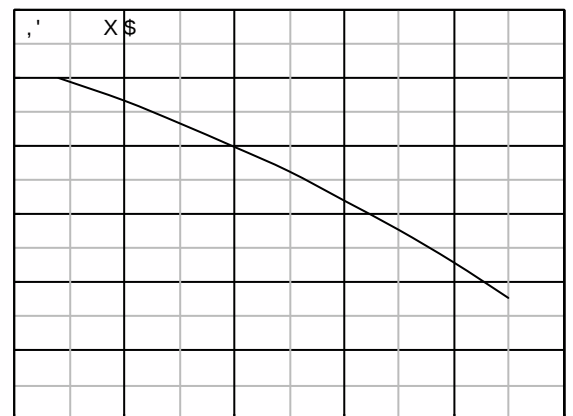
$-I_S$ - 6RXUFH WR 'UDLQ 9 ROWDJH 9

)LJXUH 6 RQ 96 'UDLQ & XUHHQW \$

)RUZDUG FKDUUUFH WHULVWLFV



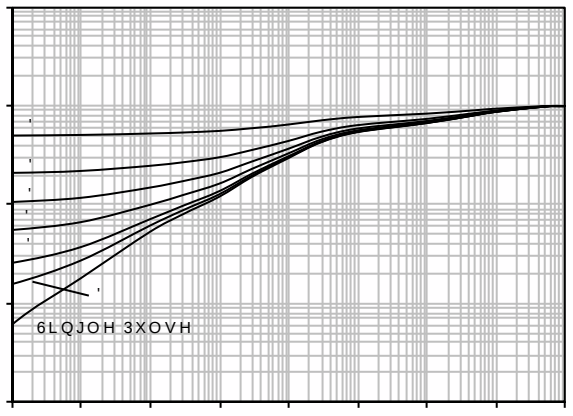
T_j -XQFWLRQ 7HPSHUDWXUH



T_j -XQFWLRQ 7HPSHUDWXUH

)LJXUH 1RUPDOLJHG 7KHUHV

)LJXUH 1RUPDOLJHG 7KHUHV



6TXDUH :DYH 3XOVH 'XUWLRQ

)LJXUH 0D[LPXP 7KHUHV

)LJXUH 6DIH 2SHUDWL

YJL2305BQ

